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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF: Wataru SAITO, et al.

SERIAL NUMBER: 10/634,917

GROUP: 2822

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EXAMINER: LEWIS, MONICA

FOR: A WIDEBAND GAP POWER SEMICONDUCTOR DEVICE HAVING A LOW ON-RESISTANCE AND HAVING A HIGH AVALANCHE CAPABILITY USED FOR POWER CONTROL

**REQUEST TO CORRECT TITLE OF INVENTION**

MAIL STOP ISSUE FEE  
COMMISSIONER FOR PATENTS  
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SIR:

In the matter of the above-identified application for patent, we hereby request correction of your records to reflect the correct title of the invention. The title of the invention should read as follows: **A WIDEBAND GAP POWER SEMICONDUCTOR DEVICE HAVING A LOW ON-RESISTANCE AND HAVING A HIGH AVALANCHE CAPABILITY** USED FOR POWER CONTROL.

Respectfully Submitted,

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